

Substitute for form 1449A/PTO

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known

Application Number	09/945500
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 1 of 2

Attorney Docket No: 01303.029US1

## US PATENT DOCUMENTS

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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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# **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

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Sheet 2 of 2

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Application Number	09/945500
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Unknown

Attorney Docket No: 01303.029US1

## **OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

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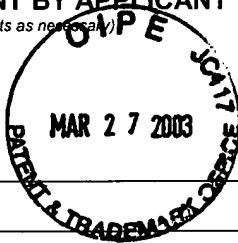
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**Application Number** 09/945500

**Filing Date** August 30, 2001

**First Named Inventor** Forbes, Leonard

**Group Art Unit** 2818

**Examiner Name** Pham, Ly

Sheet 1 of 3

**Attorney Docket No:** 1303.029US1

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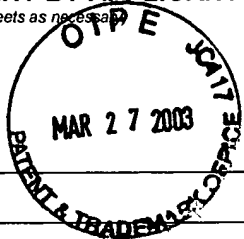
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First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Pham, Ly

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Attorney Docket No: 1303.029US1

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